



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Katsunori UENO

Serial No.: 10/646,586

Group Art Unit: 2811

Filed: August 22, 2003

Examiner:

For: SILICON CARBIDE n CHANNEL MOS SEMICONDUCTOR
DEVICE AND METHOD FOR MANUFACTURING THE SAME

Certificate of Mailing

I hereby certify that this paper is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria VA 22313-1450 on:

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Marc A. Rossi

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Pursuant to 37 C.F.R. §1.56, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached Form PTO-1449. Copies of the references listed on Form PTO-1449 are attached.


It is respectfully requested that the information be expressly considered during the prosecution of this application, that these references be made of record therein and appear among the "References Cited" on any patent to issue therefrom, and that an initialed copy of the PTO-1449 be returned to the undersigned.

Respectfully submitted,

Date: 11-19-03

[Signature]
Marc A. Rossi
Registration No. 31,923

Attorney Docket No.: FUJI:141A

<div style="text-align: center;">  <p>INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)</p> </div>	Docket Number (Optional) FUJI:141A	Application Number 10/646,586
	Applicant(s) Katsunori UENO	
	Filing Date August 22, 2003	Group Art Unit 2811

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		US 5,776,837	7/98	Palmour	438	767	
		US 5,506,421	4/96	Palmour	257	77	
		US 6,002,143	12/99	Terasawa	257	77	

FOREIGN PATENT DOCUMENTS

REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

		"Vital Issues for SiC Power Devices"; K. Hara; Materials Science Forum Vols. 264-268 (1998); pgs. 901-906; 1998 Trans Tech Publications, Switzerland
		"High Voltage Planar 6H-SiC Accufet"; P.M. Shenoy et al.; Materials Science Forum Vols. 264-268 (1998); pgs. 993-996; 1998 Trans Tech Publications, Switzerland

EXAMINER	DATE CONSIDERED
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.